

NTE287 (NPN) & NTE288 (PNP) Silicon Complementary Transistors High Voltage, General Purpose Amplifier

Absolute Maximum Ratings:

Collector–Emitter Voltage, V_{CEO}	300V
Collector–Base Voltage, V_{CBE}	300V
Emitter–Base Voltage, V_{EBO}	
NTE287	6V
NTE288	5V
Continuous Collector Current, I_C	500mA
Total Device Dissipation @ $T_A = +25^\circ\text{C}$, P_D	625mW
Derate Above $+25^\circ\text{C}$	5mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = +25^\circ\text{C}$, P_D	1.5W
Derate Above $+25^\circ\text{C}$	12mW/ $^\circ\text{C}$
Operating Junction Temperature Range, T_J	-55° to $+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-55° to $+150^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient, R_{thJA}	200 $^\circ\text{C}/\text{mW}$
Thermal Resistance, Junction–to–Case, R_{thJC}	83.3 $^\circ\text{C}/\text{mW}$

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}$, $I_B = 0$, Note 1	300	–	–	V
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$, $I_E = 0$	300	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}$, $I_C = 0$	6	–	–	V
NTE287						
NTE288			5	–	–	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 200\text{V}$, $I_E = 0$	–	–	0.1	μA
NTE287						
NTE288			–	–	0.25	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6\text{V}$, $I_C = 0$	–	–	0.1	μA
NTE287						
NTE288		$V_{EB} = 3\text{V}$, $I_C = 0$	–	–	0.1	μA

Note 1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

Electrical Characteristics (Cont'd): ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
ON Characteristics (Note 1)							
DC Current Gain NTE287 & NTE288	h_{FE}	$I_C = 1\text{mA}, V_{CE} = 10\text{V}$	25	–	–		
		$I_C = 10\text{mA}, V_{CE} = 10\text{V}$	40	–	–		
		$I_C = 30\text{mA}, V_{CE} = 10\text{V}$	NTE287	40	–	–	
			NTE288	25	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 20\text{mA}, I_B = 2\text{mA}$	–	–	0.5	V	
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 20\text{mA}, I_B = 2\text{mA}$	–	–	0.9	V	
Small–Signal Characteristics							
Current Gain – Bandwidth Product	f_T	$I_C = 10\text{mA}, V_{CE} = 20\text{V}, f = 100\text{MHz}$	50	–	–	MHz	
Collector–Base Capacitance NTE287	C_{cb}	$V_{CB} = 20\text{V}, I_E = 0, f = 1\text{MHz}$	–	–	3	pF	
			NTE288	–	–	6	pF

Note 1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

